



INTERNATIONAL ATOMIC ENERGY AGENCY
UNITED NATIONS EDUCATIONAL, SCIENTIFIC AND CULTURAL ORGANIZATION
INTERNATIONAL CENTRE FOR THEORETICAL PHYSICS
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UNITED NATIONS INDUSTRIAL DEVELOPMENT ORGANIZATION



INTERNATIONAL CENTRE FOR SCIENCE AND HIGH TECHNOLOGY

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**ICTP-INFN
SECOND COURSE ON BASIC VLSI DESIGN TECHNIQUES
18 February - 15 March 1991**

***Additional material to lectures
by***

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These are preliminary lecture notes, intended only for distribution to participants.

ADDITIONAL MATERIAL

TOPICS

TERMINATOR S.A.B.

OP AMP DESIGN

References

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OTA DESIGN

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VOLTAGE REFERENCE

(3) If desired, for achieving higher accuracy modelling of breakdown behaviour, more accurate zener models (g) may be implemented on the circuit simulator.

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the gap (etching width) between adjacent capacitor plates is more than 6 μ m, ($A = 12\mu\text{m}$).

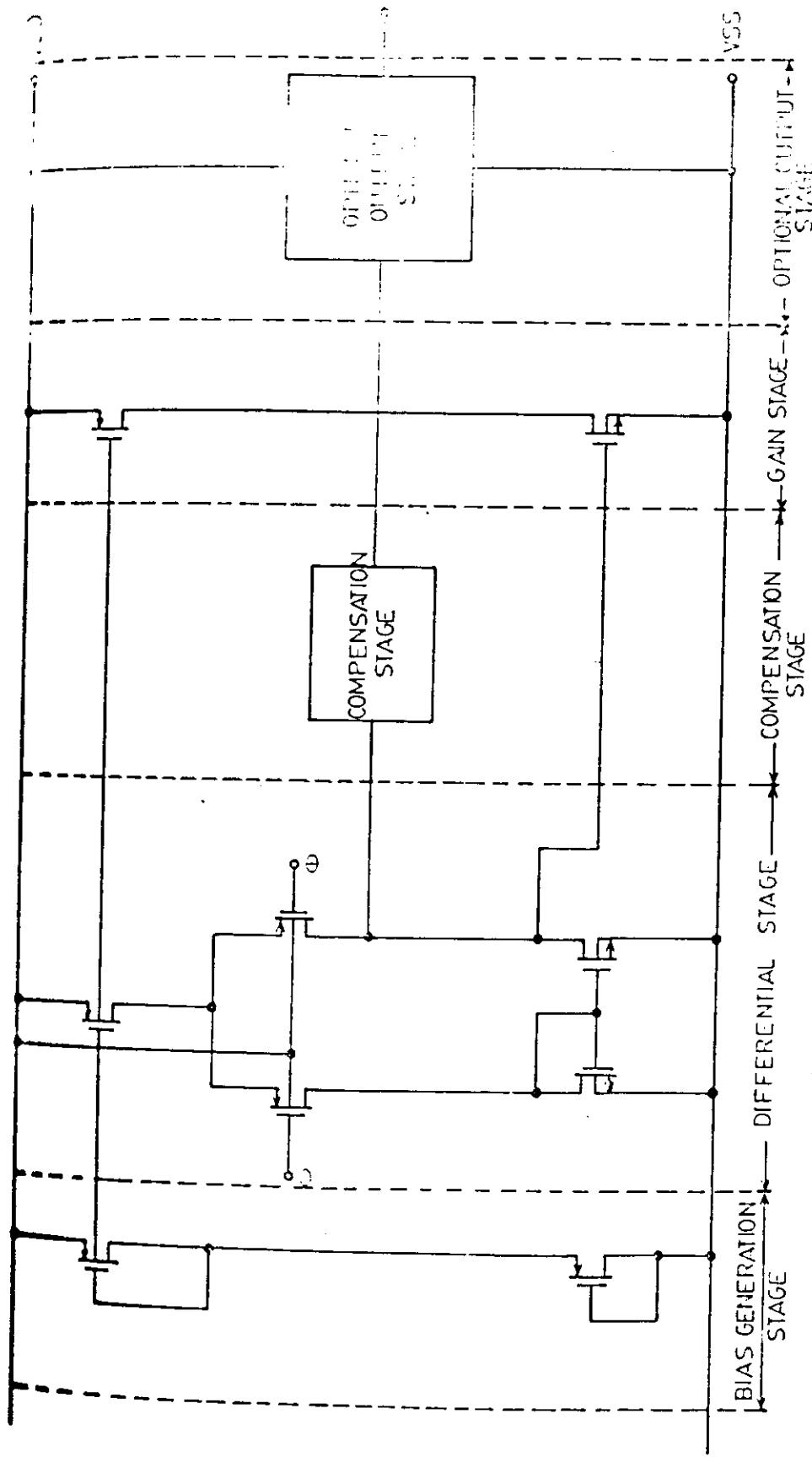
Measurements

It is intended that Measurements will be done by HP 4275A LCR meter. The most attractive feature of the instrument, which makes it suitable for low-capacitance measurements is that it can store a reference value (e.g. of a parasitic capacitance) & can later, subtract this value from the value being measured for the actual intended capacitance. Its like the zero setting of a conventional multimeter. Further it can measure the required minimum values of capacitances to an accuracy which is better than 8-bit, which is our requirement.

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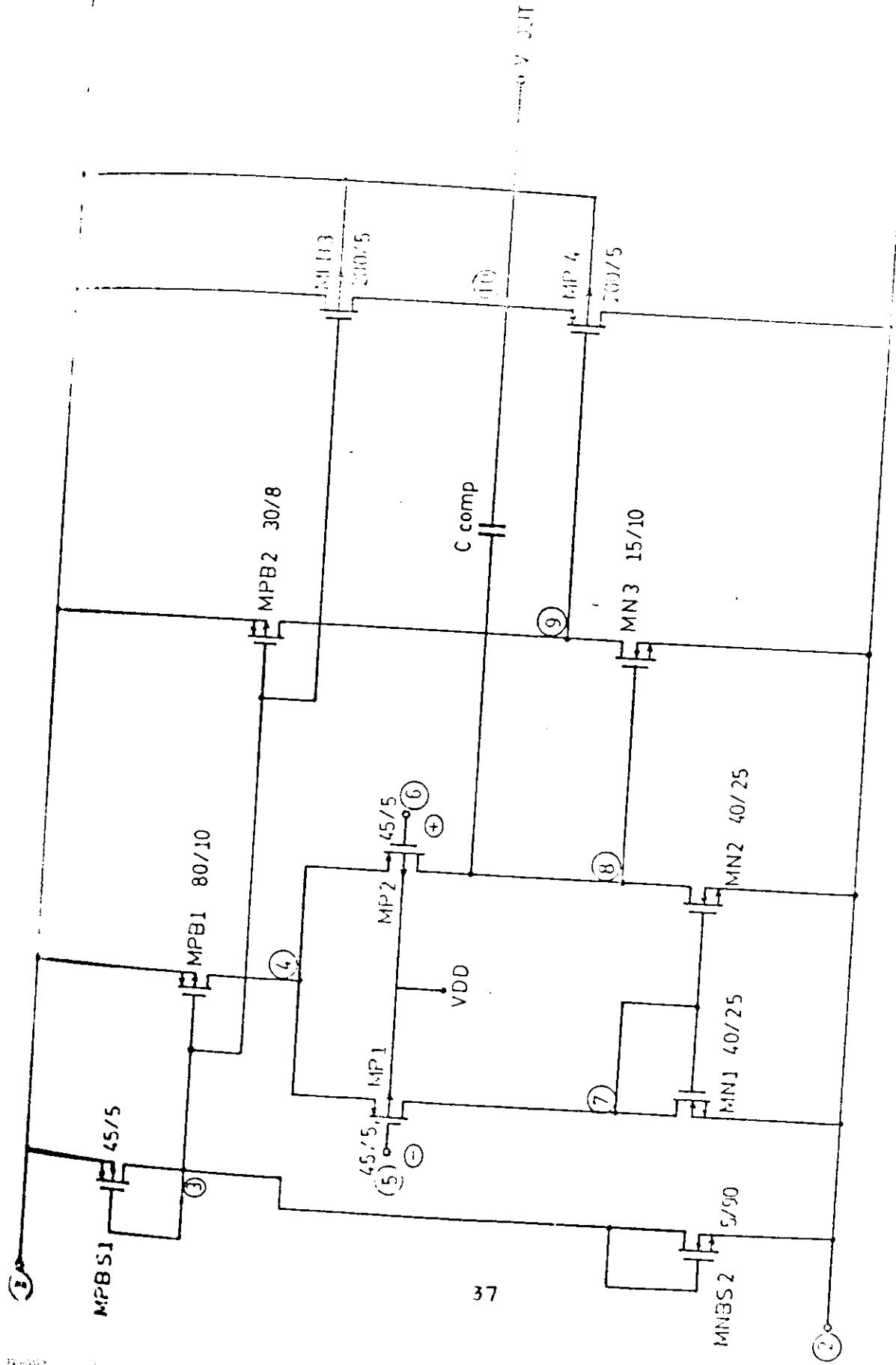
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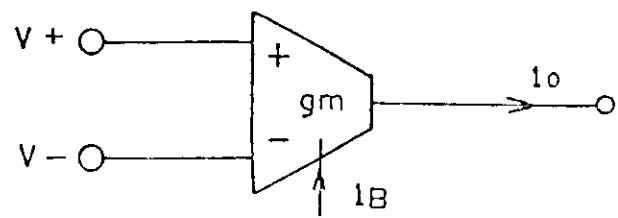
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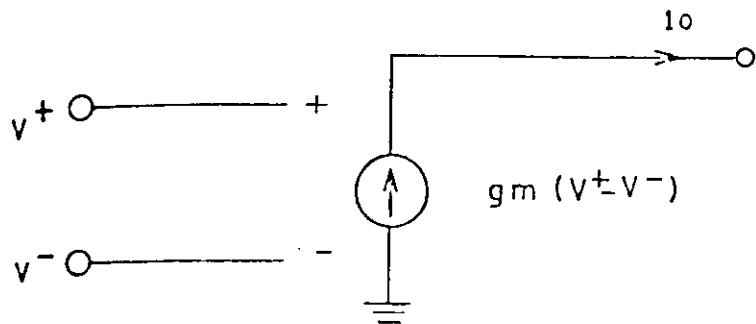
BASIC OPAMP CONFIGURATION (P-TYPE)

FIG. (d) COMPLETE OP AMP SCHEMATIC



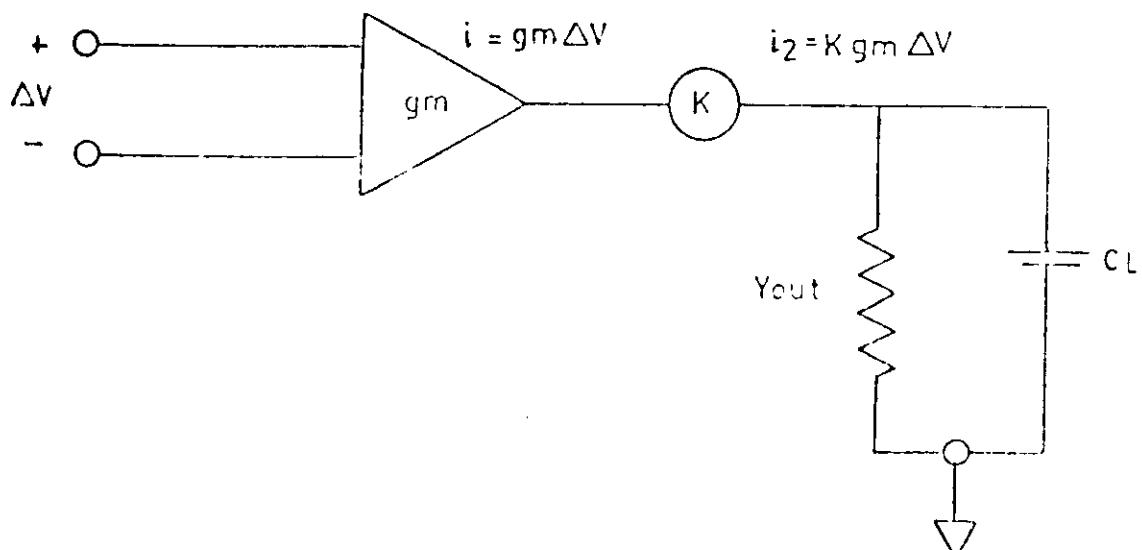


FIG(1)a : OTA SYMBOL



FIG(1)b: EQUIVALENT CIRCUIT OF IDEAL OTA

FIG.(1): OTA SYMBOL AND MODEL



FIG(2)a : OTA EQUIVALENT CIRCUIT

OPERATIONAL TRANSCONDUCTANCE
AMPLIFIER

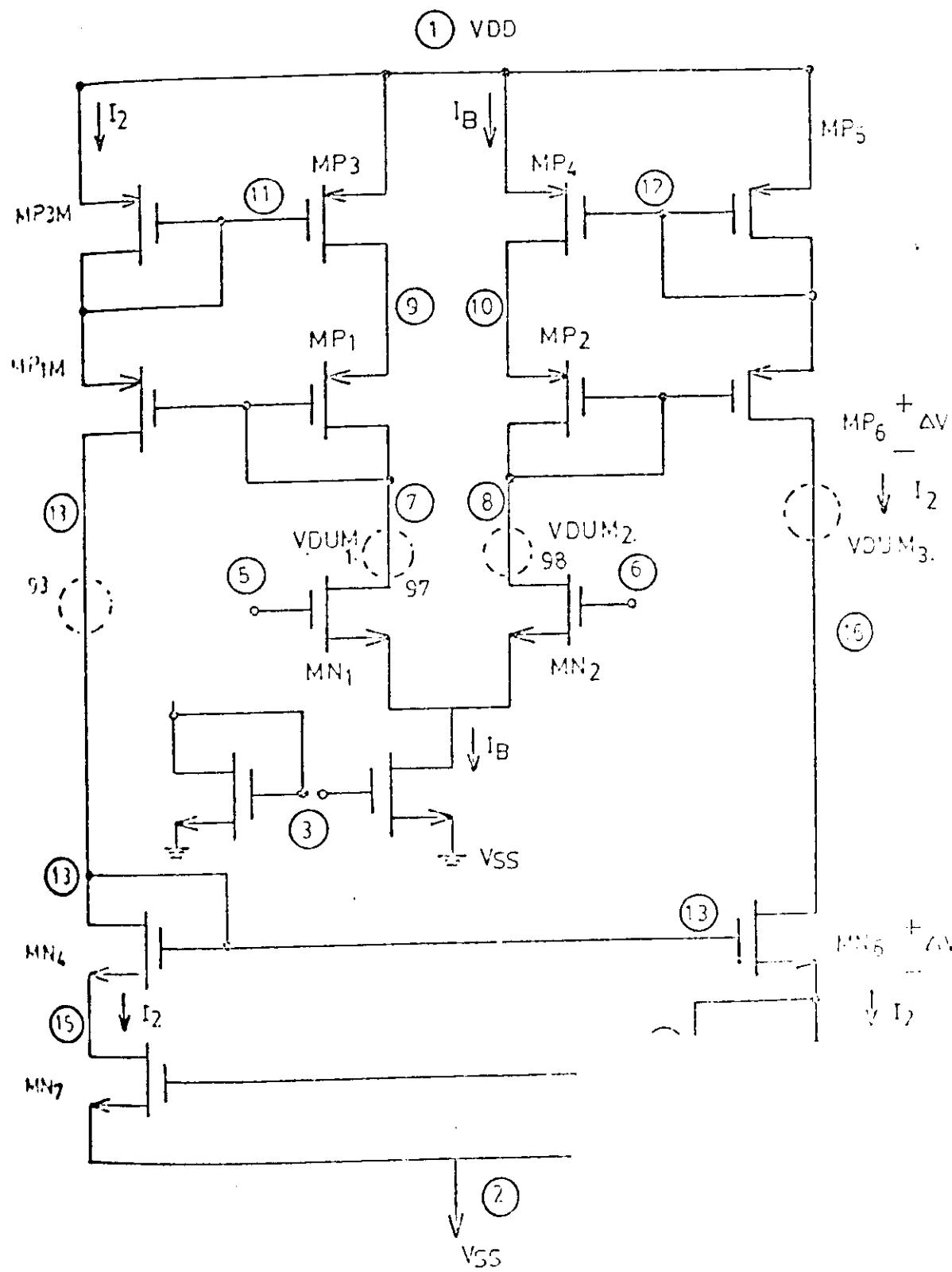


FIG.2(b): COMPARATOR CIRCUIT

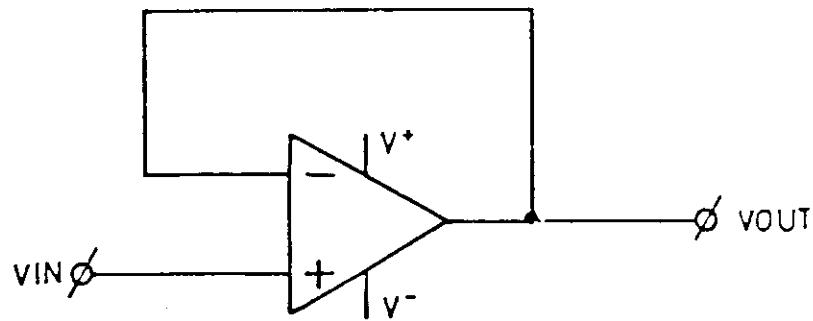


FIG. 1.(a): SYMBOL OF UNITY GAIN BUFFER

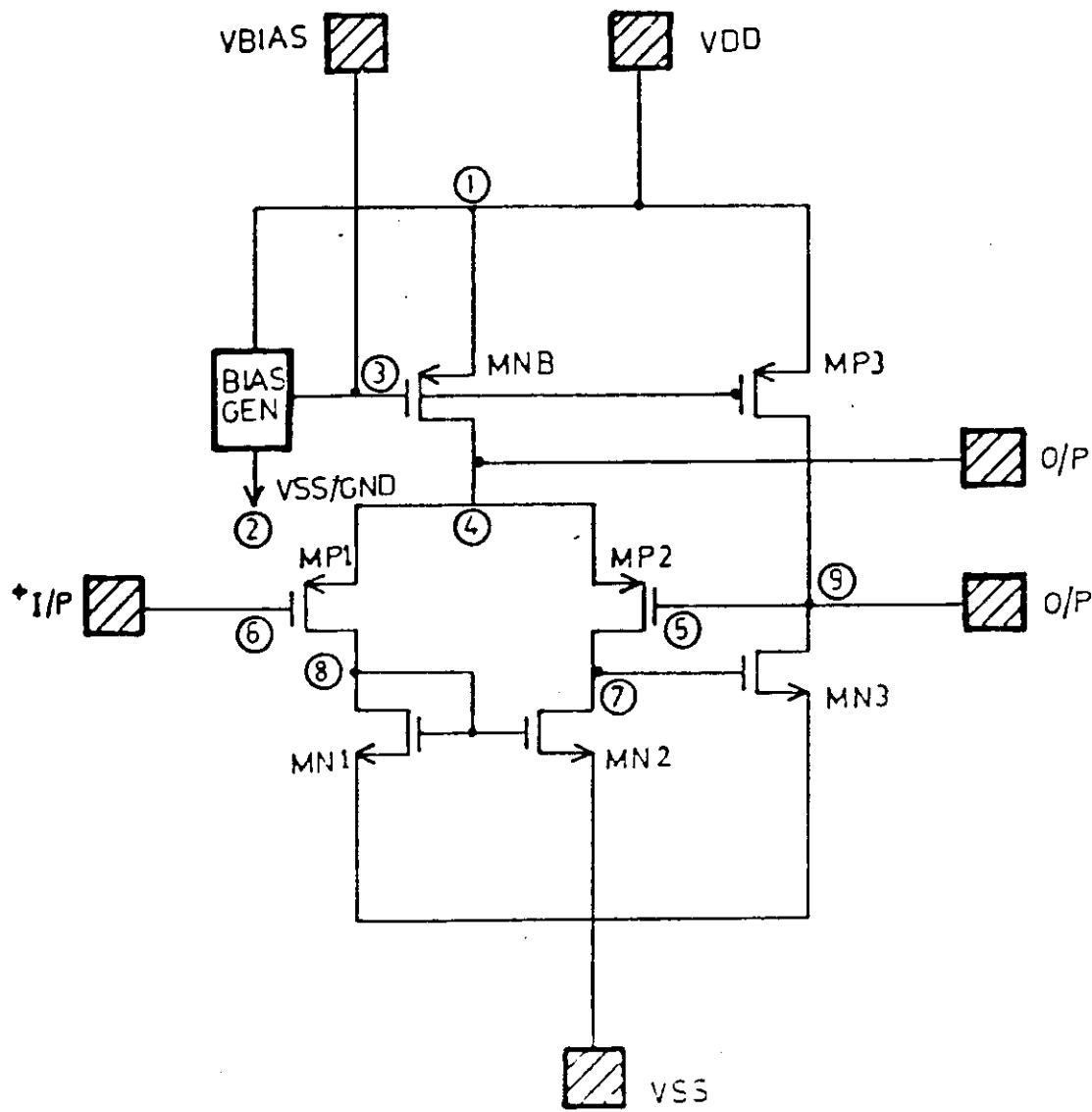


FIG. 1.(b): SCHEMATIC OF UNITY GAIN BUFFER

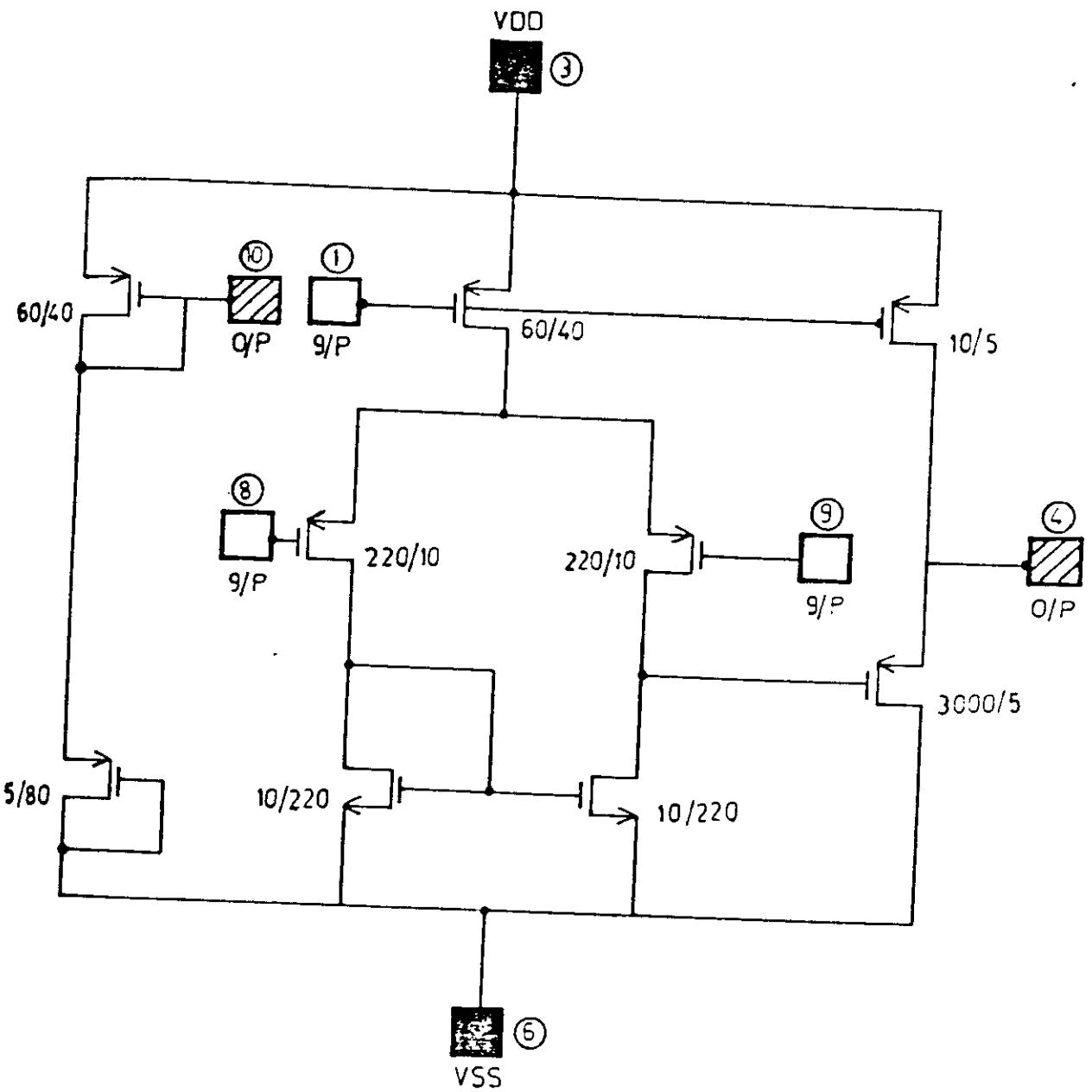


FIG. 2.: - UNITY GAIN BUFFER WITH DEVICE SIZES

